

# MEMS made in a Small Scale Research Lab – Opportunities for Functional Targets

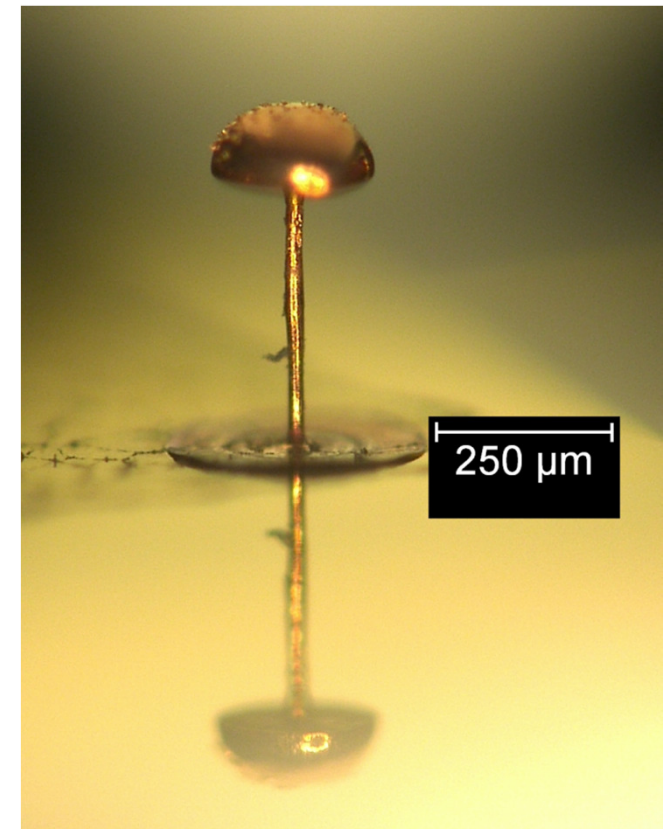


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F. Greiner, F. Dassinger, S. Quednau, H. F. Schlaak

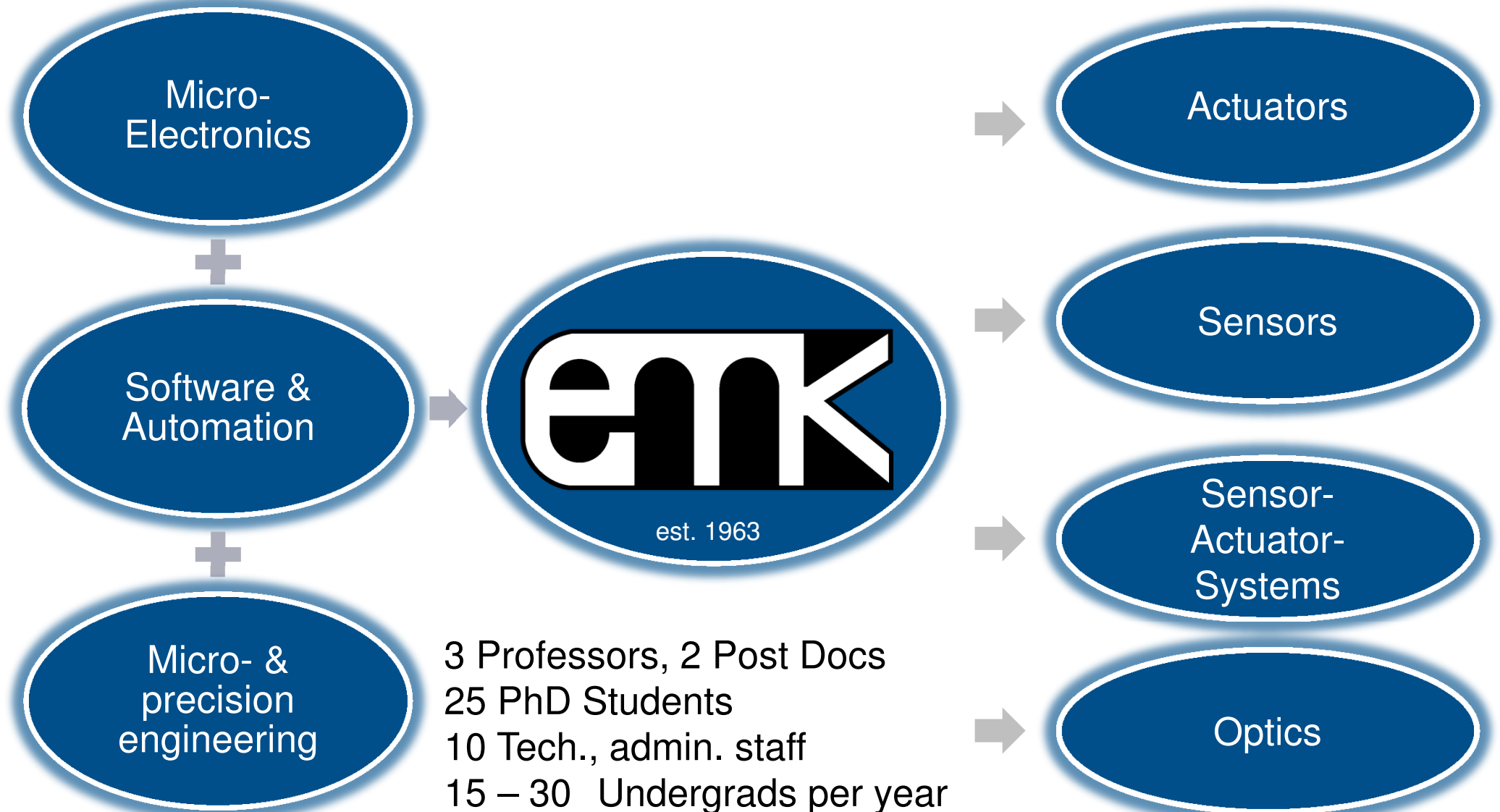
Institute of Electromechanical Design  
Institut für **Elektromechanische Konstruktionen** **EMK**

Merckstraße 25, D-64283 Darmstadt, Germany  
[www.institut-emk.de](http://www.institut-emk.de)



# Institute for Electromechanical Design – EMK

## Institut für Elektromechanische Konstruktionen



# Cleanroom Laboratory for Microtechnology



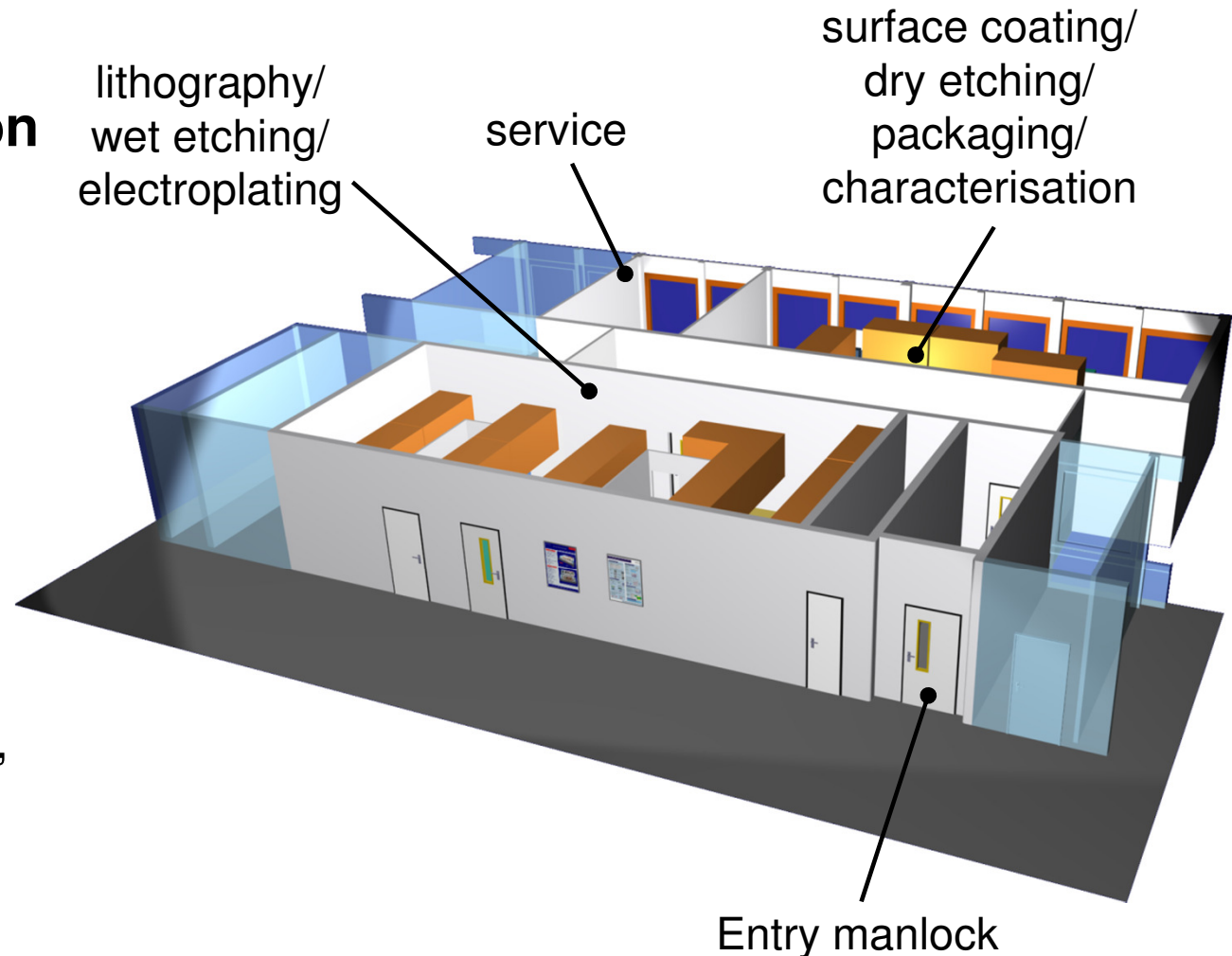
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## Clean room classification

1.000 - 100 within the  
laminar airflow boxes

## Functionality

- about 60 m<sup>2</sup> for  
photolithography,  
wet etching, electroplating
- about 60 m<sup>2</sup> for  
packaging, surface coating,  
measurement



<http://www.emk.tu-darmstadt.de/en/institute/equipment/>

# Technology Overview

## Substrate Pretreatment



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### Sputtering



#### Alcatel

- DC/ HF Sputtering with RF-Bias
- 4 Cathodes
- Al, Cr, Cu, SiO<sub>2</sub>
- Deposition Rates up to 1000 nm/min
- Vacuum Prechamber

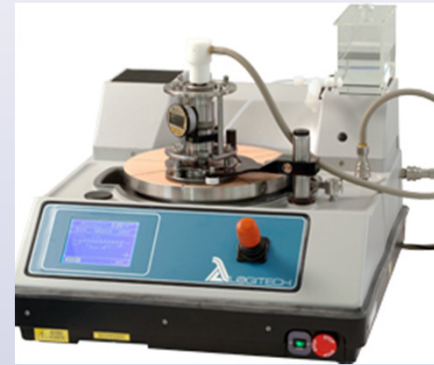
### Vapour Deposition



#### Balzers BAK 600

- Electron Beam and Resistance Evaporator
- Al, Cu, Cr, Ni, Ag, Ti, Au, Al<sub>2</sub>O<sub>3</sub>
- Thickness Control through Quartz Resonator

### Polishing Machine



#### Logitech PM5

- Precision Polishing Jig with vacuum adapter
- Up to 4" wafer
- Plate Speed: 0-70 rpm
- Chemical Mechanical Polishing option

# Technology Overview

## UV-Lithography I



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### Spin Coater



#### SÜSS Delta 80 BM

- Rotating Lid
- Up to 4000 rpm

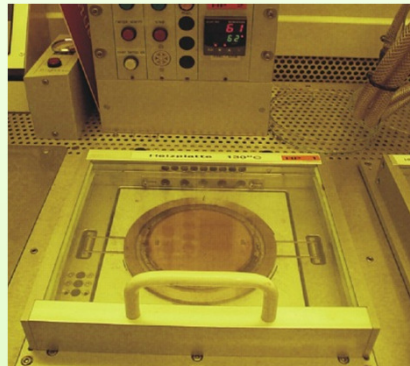
#### SÜSS LabSpin 6

- Up to 8000 rpm

#### Photo Resists

- SU-8 2000/3000
- AZ 9260
- AZ 15, 125 (n)XT

### Hotplates



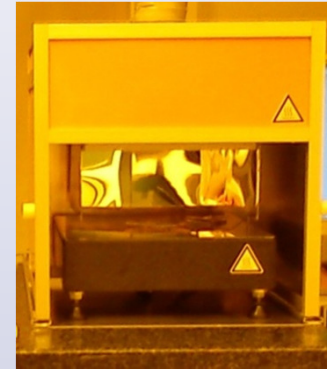
#### 2x Hotplate 400

- Programmable  
Single Plate
- Up to 130 °C

#### 3x GESTIGKEIT PR 5-3T

- Programmable  
Double Plate
- Up to 300 °C

### IR Oven



#### FH Zwickau

- IR dry system for photoresist
- Up to 6" wafer
- Max. heat 130 °C
- Maximum substrate weight 150 g

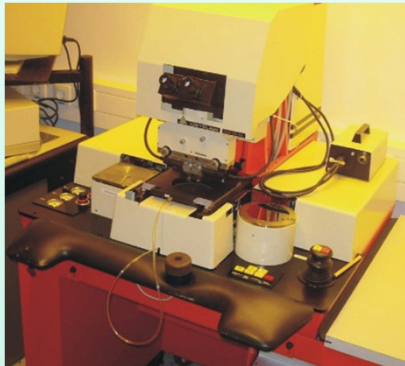
# Technology Overview

## UV-Lithography II



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### Mask Aligner



#### SÜSS MA 56 M

- 350 W UV-Lamp
- Up to 4" Masks
- Manual Alignment
- Up to 20 mW/cm<sup>2</sup>
- Process Monitoring

#### Filters

- g, h, i - Line
- g, h - Line
- i - Line

### Developer



#### Sonosys 500

- Frequency 1 MHz
- Power 50 - 500 W

#### Multi-Bio-3D

- Orbital Shaker

#### Developer

- mr-Dev 600
- MIF 326, 826
- AZ 400k

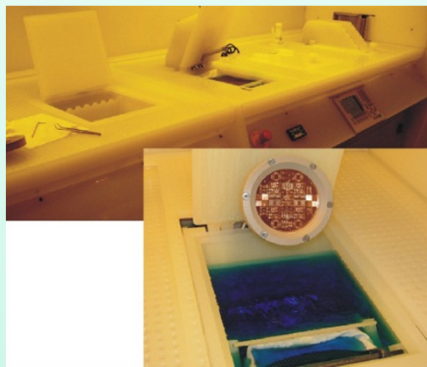
# Technology Overview

## Micro- and Nano Electroplating



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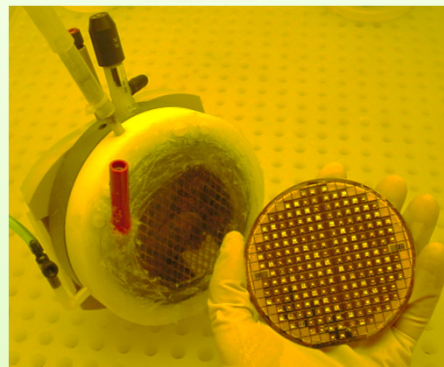
### Micro Electroplating



#### M-O-T $\mu$ Galv

- Additive free Electrolytes
- Nickel (pH 4), Copper (acid)
- Currents up to 10 A
- Puls-Plating Option
- Plating rate up to 4  $\mu\text{m}/\text{min}$

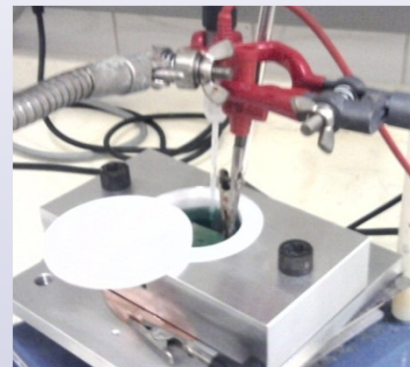
### Micro & Nano Electroplating



#### silicet trio clip

- 3 electrodes cell for 4" wafer
- Ion membrane for use with additives
- 1  $\mu\text{A}$  - 3 A reverse pulse plating to extend to 100 kHz
- 2 l volume with particle filter

### Nano Electroplating



#### Nano Electroplating Cell

- Potentiostatic and Galvanostatic Plating
- Pulse- & Reverse-Puls-Plating up to 100 kHz
- Currents down to several nA

# Technology Overview

## Plasma Activation & Etching

### Isotrop Etching



#### Muegge STP 2020

- Remote Downstream Plasma Reactor for Polymer Etching (e.g. SU-8, BCB)
- $O_2$ ,  $CF_4$ ,  $N_2$
- RF-Power: 3000 W at 13,56 MHz

### Anisotrop Etching



#### Plasma Technology RIE80

- Parallel Plate Reactor for Substrate Cleaning and Polymer Etching
- $O_2$ ,  $CF_4$ ,  $N_2$
- RF-Power: 300 W at 13,56 MHz

### Surface Activation



#### Technics 300-E Plasma

- Barrel Reactor for Substrate Cleaning and Surface Activation
- $O_2$ ,  $CF_4$ ,  $N_2$
- RF-Power: 300 W at 13,56 MHz

### Wet Etching Machine



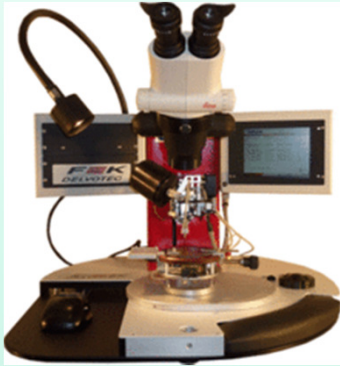
#### BUNGARD, Splash Center

- Etching medium: Fe-III-Cl
- Line definition: 100  $\mu m$
- Max. board size: 210 x 300 mm

# Technology Overview

## Packaging Technologies

### Wire Bonder



#### F&K Delvotek 53xx-BDA Bonder

- Ball Bonding down to 18  $\mu\text{m}$  gold wire
- Deep access wedge bonding
- Automated y-axis for automated loops

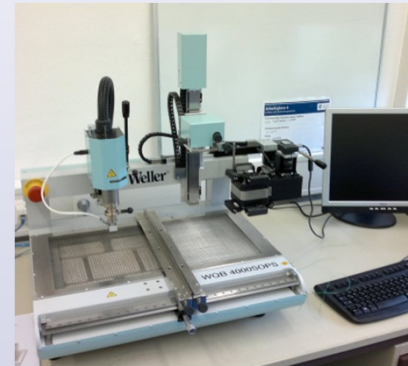
### Micro Assembly



#### Arteos TOMM 1

- Pic and placer
- Plate- and air-heater
- UV-curing
- Micro-dispenser
- Vacuum chuck

### Pick and Place



#### Cooper Hand Tools WQB 4000SOPS

- Operating range 630 x 630  $\text{mm}^2$
- Soldering temperature 50 - 400  $^{\circ}\text{C}$
- Down to smallest package sizes

### Vacuum Furnace



#### Heraeus, Nabertherm & Co

- Vacuum option
- Protective gas option e.g. N
- Temperature profile option
- High temperatures up to 1100  $^{\circ}\text{C}$

# Technology Overview

## Optical Inspection & Characterization

### Thermography



#### FLIR SC655

- 640 x 480 Pixel
- -20 °C to +150 °C  
0 °C to 650 °C
- Sensitivity:  
<0.05 °C @ +30 °C

### Optical Inspection



#### Keyence VHX-600

- 3CCD Camera
- 54 Mio Pixel
- Magnification up to 1000x
- 3D Measurement Option
- Measurements of Structural Widths

### Laser Vibrometer



#### Polytec OFV 2502

- 2 sensor heads (OFV 534)
  - Velocity demodulation
  - 1.5 MHz
- #### Polytec OFV 3001
- Velocity demodulation
  - 0.3  $\mu\text{m/s}$ ... 10 m/s

### High Speed Camera



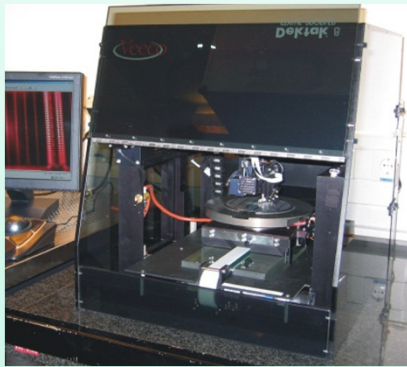
#### Mikro GmbH

- 1280x1024 pixel
- 502 fps
- 55 min recordtime

# Technology Overview

## Electro Mechanical Characterization I

### Surface Profiler



#### DEKTAK 8 Profiler

- Measurement of Layer Thickness and Surface Profile
- Range from 10 nm up to 1 mm
- Stylus Force up to 0,09 mg

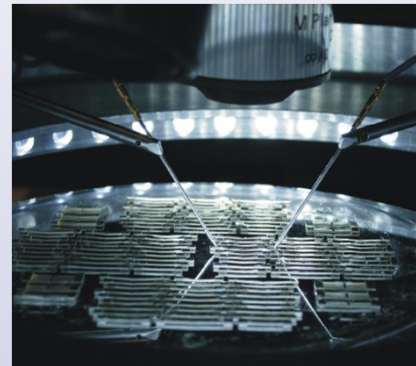
### Bond Shear Tester



#### dage Microtester 22

- Testing strength of solder joints, wire bonds and more
- Stitch Test Failure Detection
- 20 gm & 10 kg Load
- Resolution +/- 0,5% of load

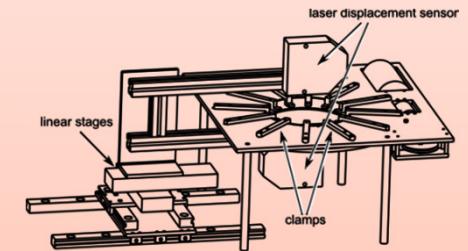
### Motion-Analyzer



#### MEMS-Analyzer

- 2048 x 2048 Pixel
- 15 fps, 800 MBit/s
- Repeatability < 30 nm
- Force Measurements up to 1 N
- Field of View up to 11,7 x 11,7 mm<sup>2</sup>

### EAP Characterization



#### EAP-Analyzer

- Static / dynamic deflection (line scan)
- Frequency response
- Preload simulation
- Sheet resistance
- Force-displacement

# Technology Overview

## Electro Mechanical Characterization II



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### High-Pressure Static Tester



#### **COP-7000**

- 500 MPa=5000 bar
- silicon oil
- Room temperature

#### **Pressure sensor**

- P3MBP 5000 bar (HBM)

#### **Piston gauge**

- 5ppm @ 5 000 bar
- 1 kg / 50 bar

### High-Pressure Dynamic Tester



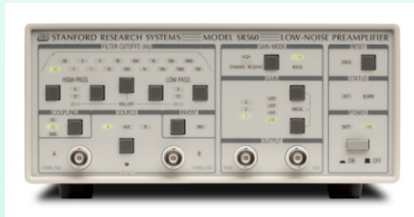
#### **MAXIMATOR**

- up to 1000 bar
- Periodic load at 0.1 Hz to 20 Hz
- Curve shape rectangular, trapezoid or sinus
- 4 pressure connectors

# Technology Overview

## Electrical Measurement Equipment

### Signal Conditioning



#### Stanford Research SR 560

- low-noise preamplifier
- battery operating option

#### Krohn-Hite 3382

- programmable dual-channel filter
- 0.1 Hz – 200 kHz
- Butterworth or Bessel response

### Impedance Analysis



#### Agilent 35670A

- dynamic signal analyzer
- 122  $\mu$ Hz - 102.4 kHz, 16-bit
- swept sine option
- GPIB

#### HP 4284 A

- Precision LCR-Meter
- 20Hz – 1 MHz
- GPIB

### DAQ-Systems



#### Data Acquisition

- DMM, LCR-Meter
- Multi-Purpose DAQ (16 bit, 1,25 MSa)
- 8ch Bridge Input Module (24 bit, 25 kSa)

#### Universal Control

- PXI, cRIO
- AI, AO, DIO, SPI, Bridge

### Peripherals



#### LeCroy

#### WaveRunner 44Xi-A

- 400 MHz, 5 GSa

#### Agilent DSOX3024A

- 200 MHz, 4GSa

#### Hameg HMP4040

- programmable power supply

#### Hameg HMF2525

- 25 MHz Arbitrary Signal generator

# High AR Metal Pillars UV Direct LIGA Processing

Si + SiO<sub>2</sub>   
  Cr   
  Al  
 Cu   
  SU-8   
  AZ 125nXT

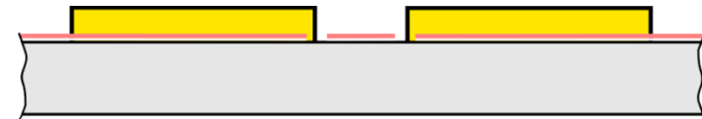


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- Structured electrode layer: Cr + Cu 100 nm



- Sacrificial layer: SU-8 5 μm

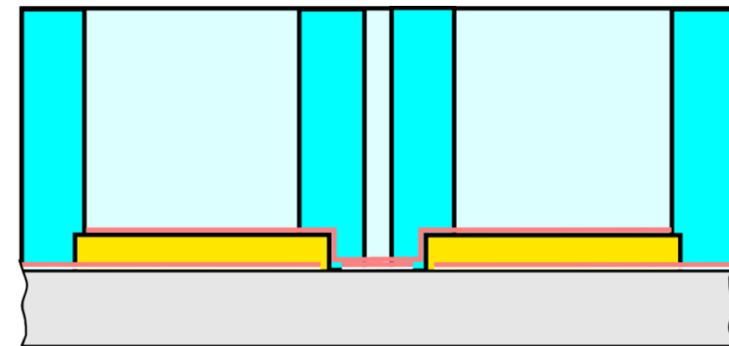


- Structured seed layer:  
Cu 200 nm + Al 20 nm



- Exposed photoresist, undeveloped:  
AZ125nXT 400 μm

$$l_W = 400 \mu\text{m}, d_W = 30 - 50 \mu\text{m}$$



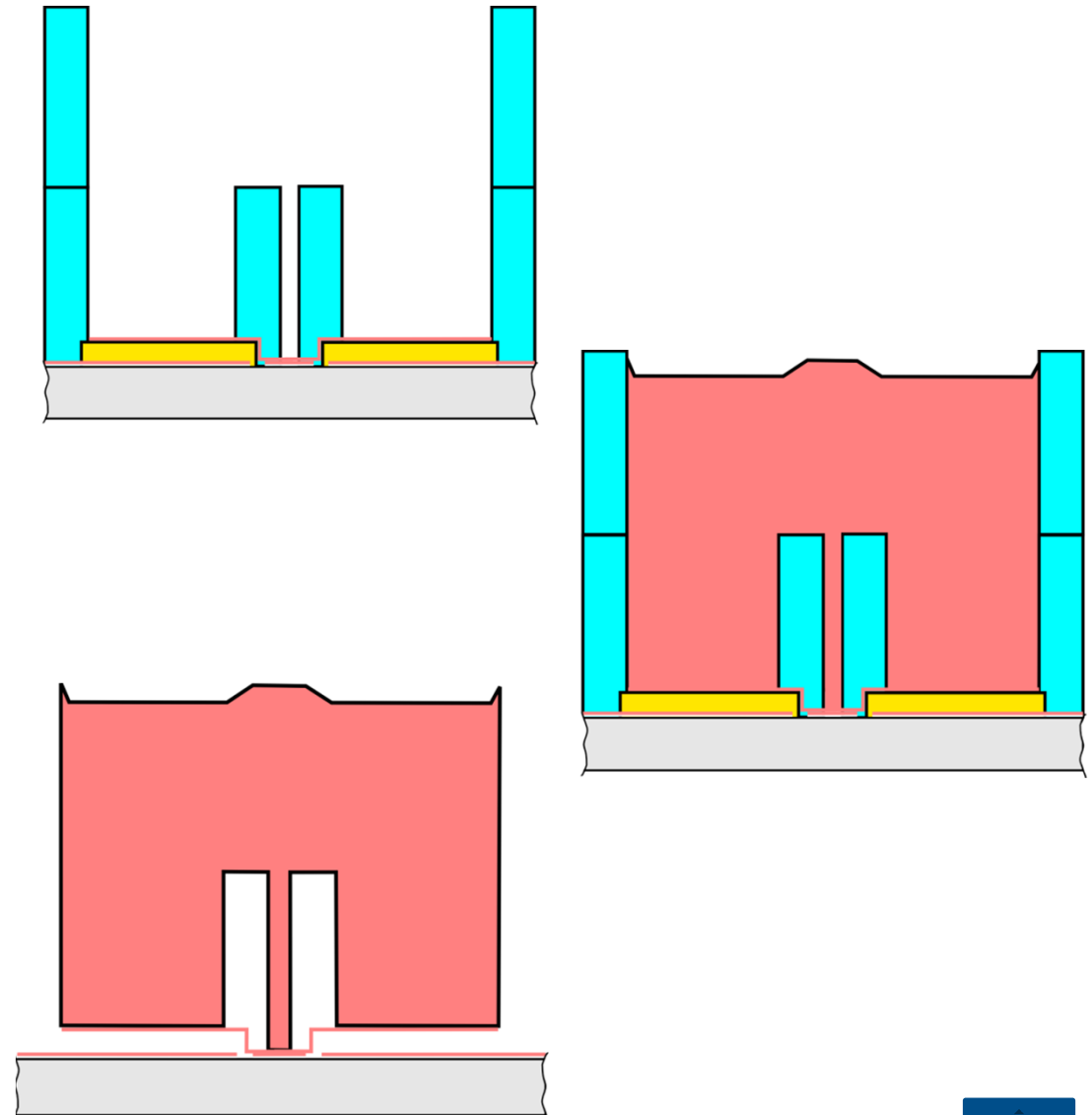
# High AR Metal Pillars UV Direct LIGA Processing

■ Si + SiO<sub>2</sub>   ■ Cr   ■ Al  
■ Cu   ■ SU-8   ■ AZ 125nXT



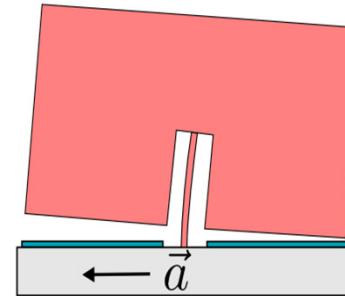
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- Structured mold for electroforming:  
AZ125nXT 2 x 400 μm
- Filled mold: 700 μm Cu
  - Current: DC, pulse, pulse reverse
  - Contacting: pillars and blocks  
grown simultaneously
- Stripping
  - Dry etching with  
reactive oxygen radicals  
(muegge/R3T)

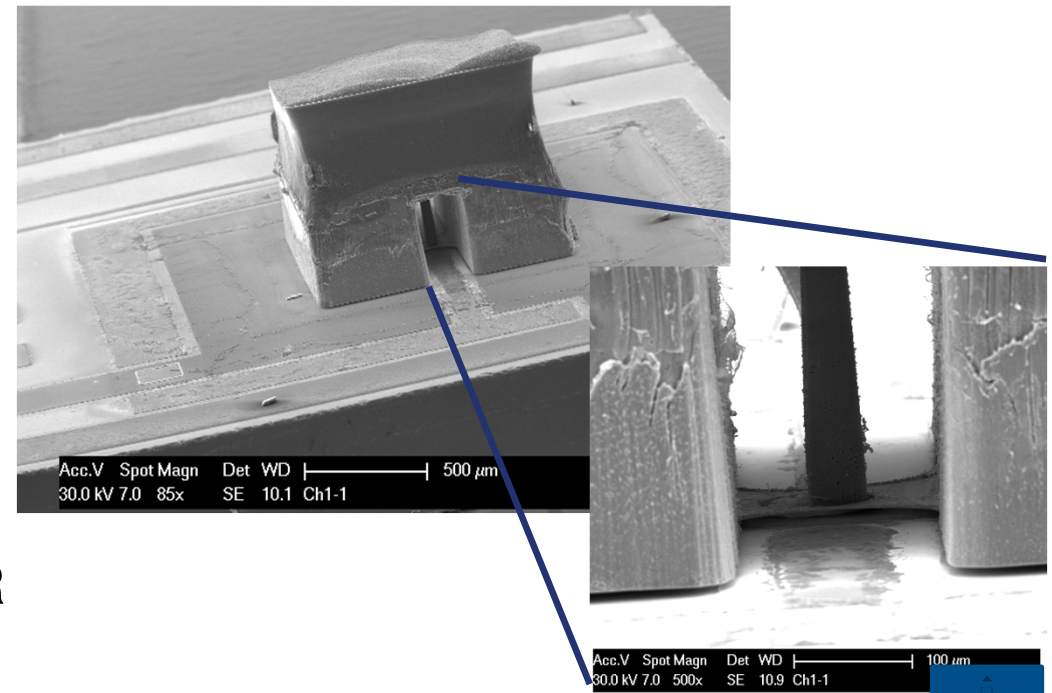


# High Aspect Ratio (AR) Metal Pillars for Minimal Footprint MEMS Suspension

- Inertial sensor
  - 1 device: 2 axes acceleration sensor and 1 axis gear rate sensor
  - Acceleration: seesaw
  - Gear rate: crosstalk due to Coriolis force



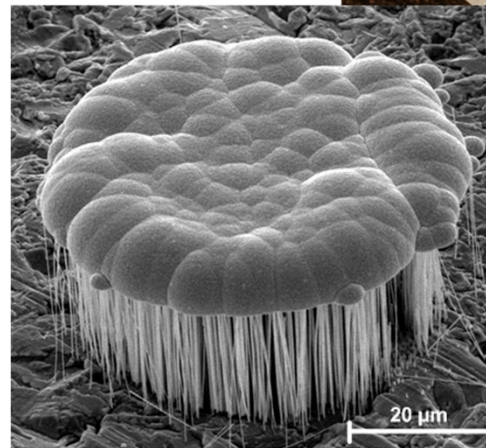
- Scale-bridging: wire diameter ( $d$ )
  - UV lithography:  $d = 40 \mu\text{m}$ , AR 10:1
  - XR lithography:  $d = 4 \mu\text{m}$ , AR 25:1
  - IT lithography:  $d = 400 \text{nm}$ , AR 75:1
- Focus on technology
  - Galvanoform with high Aspect Ratio and multiple layers
  - Electroplating with heterogenous AR



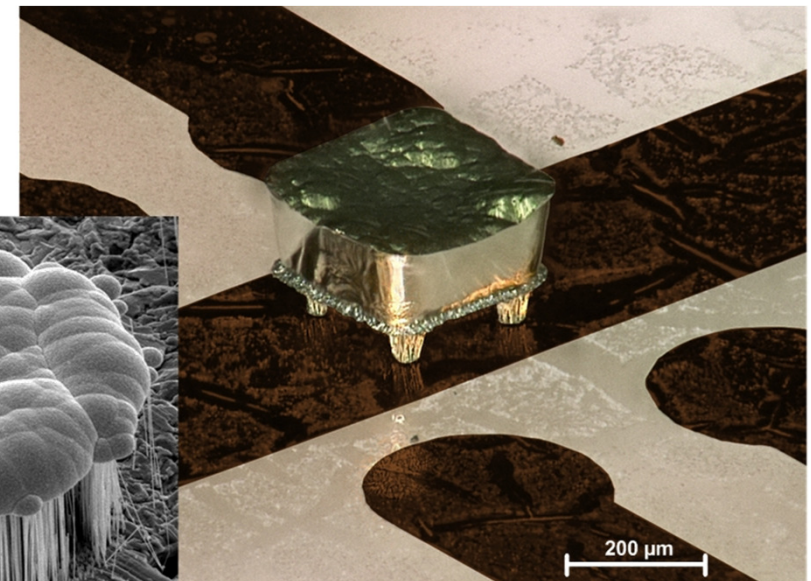
# ELEMENT - Electromechanical Sensors Based on One-Dimensional Nanostructures

## Development of an inertial sensor

- Use of high elastic nanowires with very high aspect ratio (500:1)
- Assembling nanowire-arrays (50  $\mu\text{m}$  diameter) as spring elements
- Nanoscale enables the use of noble metals with excellent physical properties
- Detection of the inertial mass displacement using a magnetoresistive sensor principle

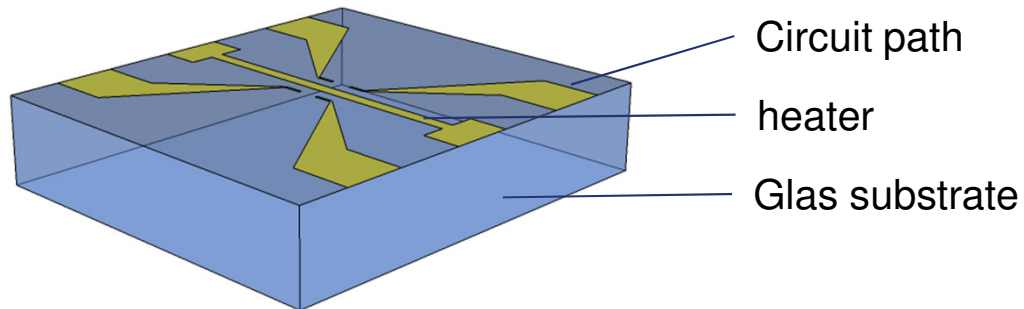


Platinum nanowire array,  
wire diameter: 150 nm

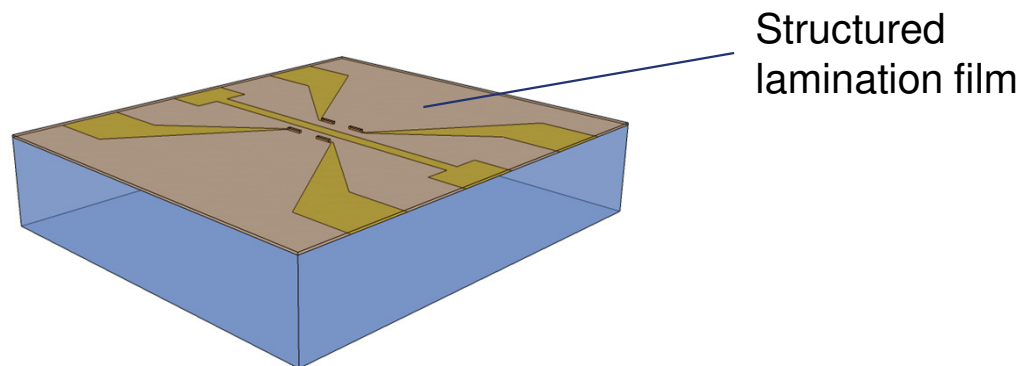


Nickel structure on  
vertical wire arrays

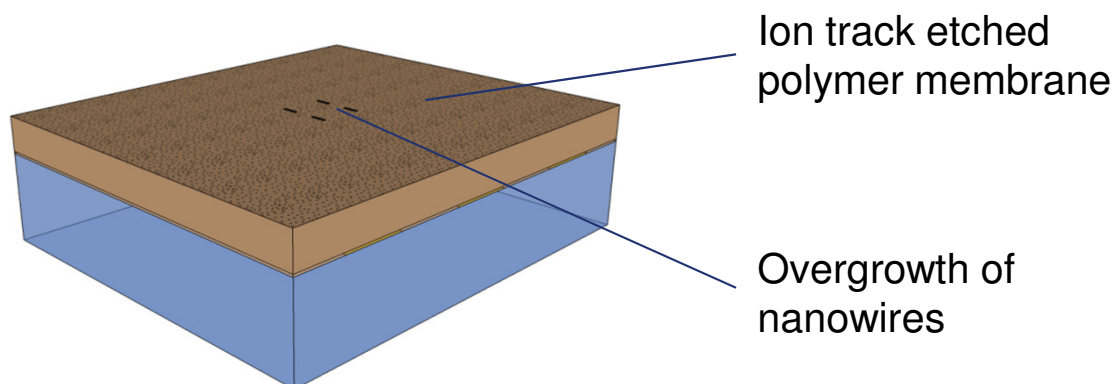
# Process for batch nanowire integration in micro systems



- Structuring of heater and circuit paths for the nanowire arrays

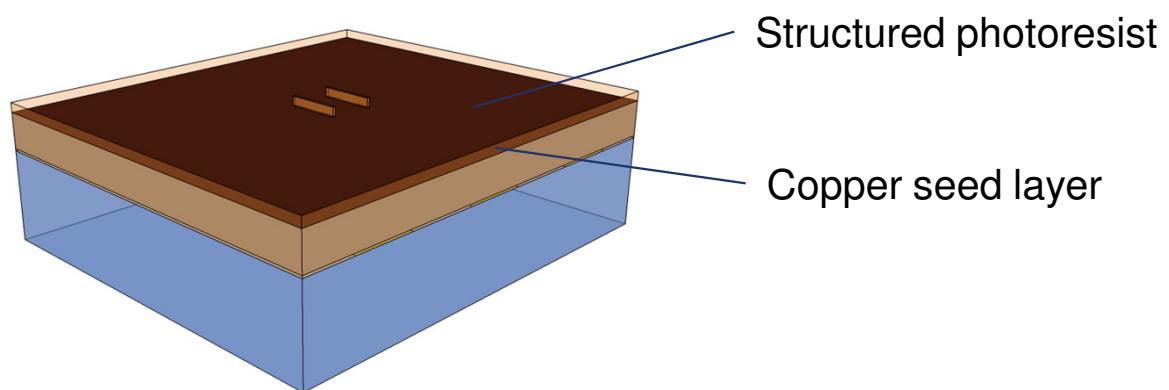


- Application of a lamination film
- Structuring of holes for uncovering the seed layer

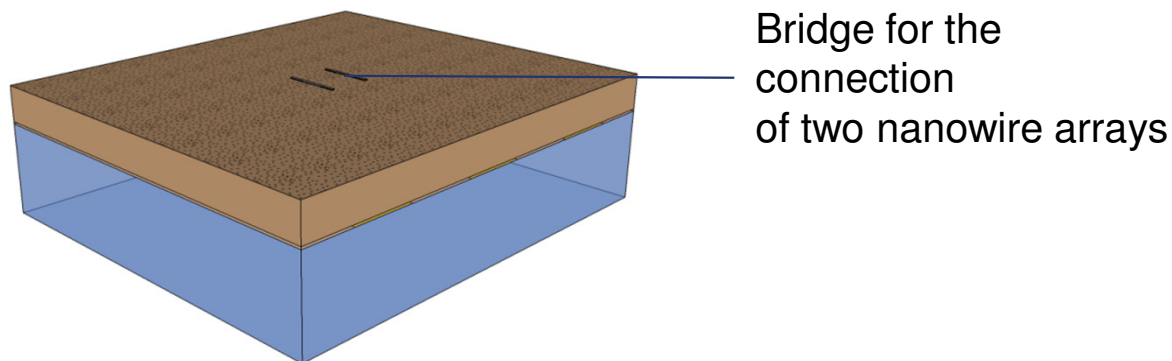


- Lamination of the ion track etched polymer template
- Electrodeposition into the pores until overgrowth

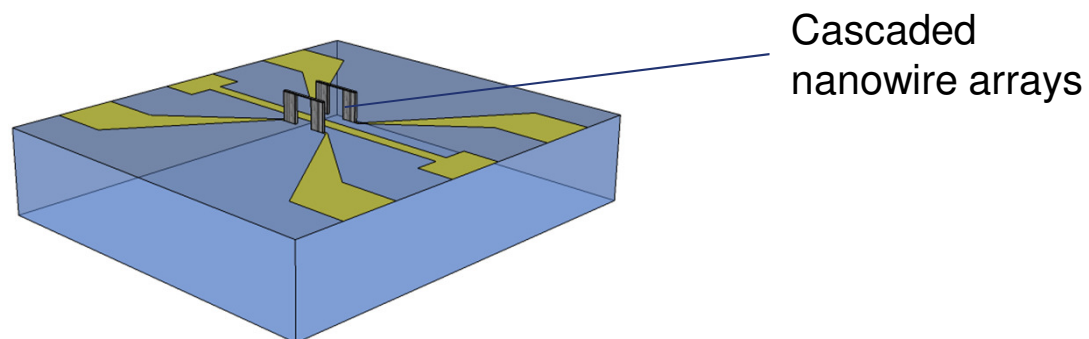
# Process for batch nanowire integration in micro systems



- Application of the Cu seed layer
- Application and structuring of the photoresist that acts as a mold for the bridge
- Electroplating of the bridge



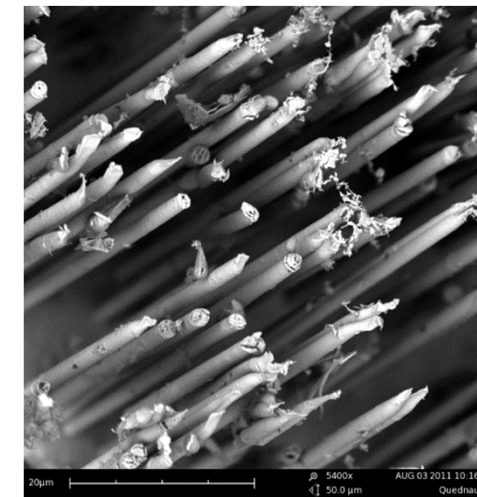
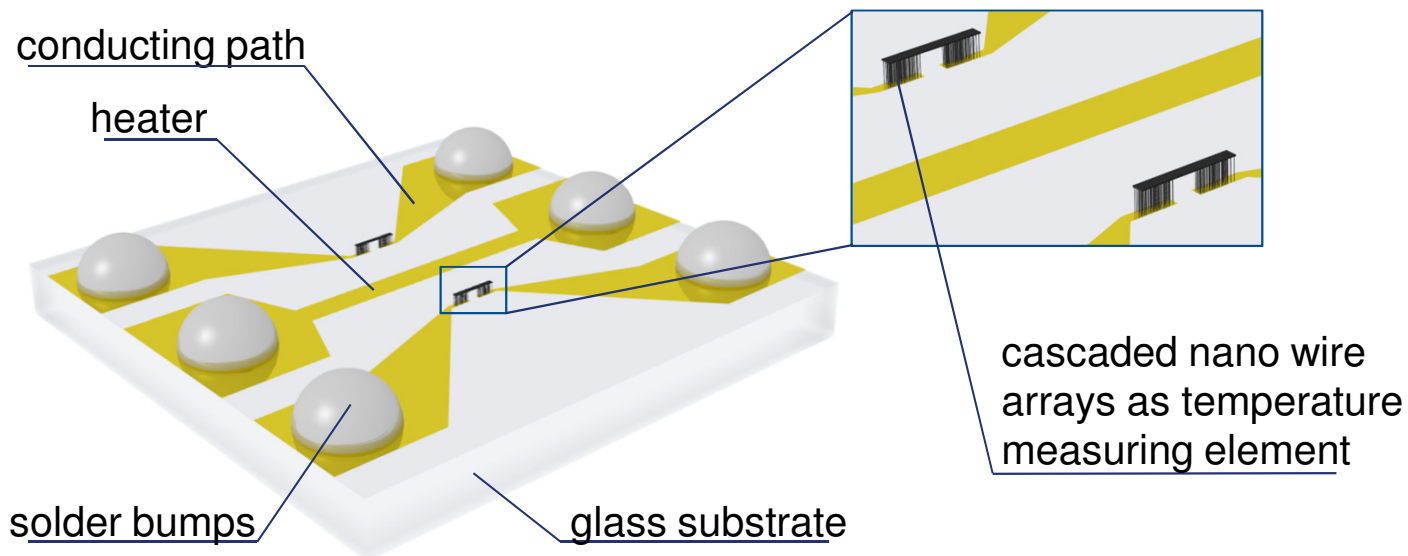
- Stripping of the photoresist
- Etching of the Cu seed layer



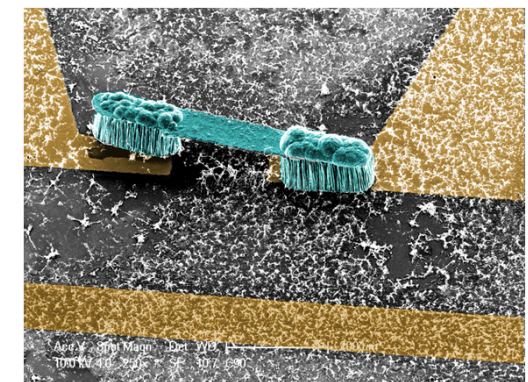
- Removal of the polymer template
- Removal of the lamination film

# 3-DOING – 3-Dimensionale Mikro-Nano-Integration für die Gasflusssensorik

- Funded Project by BMBF, VDI/VDE-IT
- Duration: 01/2011 – 12/2013
- Development of a gas flow sensor which uses metallic nano wires as sensitive elements
- Improvement of the measurement performance, especially for photoacoustic devices



Integration of metallic nano wires in micro systems



cascaded nano wire arrays

# Questions?



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